SKN 60F



Stud diode

Fast Recovery Rectifier Diode

SKN 60F SKR 60F

Features

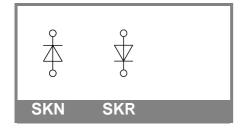
- · Small recovered charge
- Soft recovery
- Up to 1500 V reverse voltage
- Hermetic metal case with glass insulator
- Threaded studs ISO M6 and M8
- SKN: anode to stud; SKR: cathode to stud

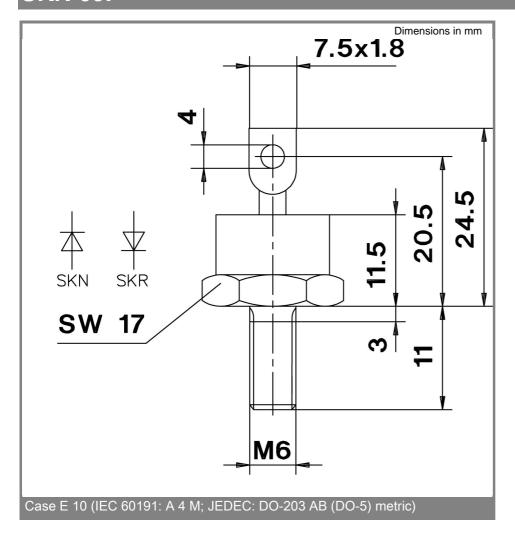
Typical Applications

- Inverse diodes for power transistors, GTO thyristors, asymmetric thyristors
- SMPS, inverters, choppers
- A.C. motor control, uninterruptible power supplies (UPS)

V_{RSM}	V_{RRM}	I _{FRMS} = 120 A (maximum value for continuous operation)		
V	V	I_{FAV} = 60 A (sin. 180; 1000 Hz; T_c = 100 °C)		
1200	1200	SKN 60F12	SKR 60F12	
1400	1400	SKN 60F14	SKR 60F14	
1500	1500	SKN 60F15	SKR 60F15	
1700	1700	SKN 60F17	SKR 60F17	

Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 85 (100) °C	75 (60)	Α
I_{FAV}	K3; T _a = 45 °C; sin. 180; 1000 Hz	21,5	Α
I _{FSM}	T _{vi} = 25 °C; 10 ms	1400	Α
	T_{vi}^{3} = 150 °C; 10 ms	1200	Α
i²t	T _{vj} = 25 °C; 8,3 10 ms	9800	A²s
	T _{vj} = 150 °C; 8,3 10 ms	7200	A²s
V _F	T _{vi} = 25 °C; I _F = 150 A	max. 1,75	V
$V_{(TO)}$	T _{vi} = 150 °C	1	V
r _T	T _{vj} = 150 °C	4	mΩ
I_{RD}	$T_{vj} = 25 ^{\circ}C; V_{RD} = V_{RRM}$	max. 0,4	mA
I_{RD}	T_{vj} = 150 °C; V_{RD} = V_{RRM}	max. 60	mA
Q _{rr}	T _{vi} = 150 °C, I _F = 100 A,	75	μC
I_{RM}	$-di/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$	70	Α
t _{rr}		2100	ns
E _{rr}		-	mJ
R _{th(j-c)}		0,5	K/W
R _{th(c-s)}		0,25	K/W
T _{vj}		- 40 + 150	°C
T _{stg}		- 55 + 150	°C
V _{isol}		-	V~
M_s	to heatsink	2,5	Nm
а		5 * 9,81	m/s²
m	approx.	20	g
Case		E 10	





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